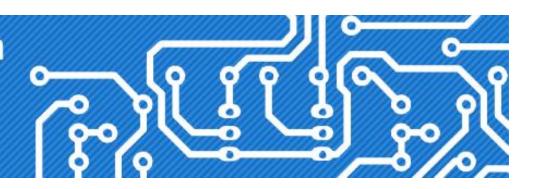
International Symposium on Physical Design



Recent Progress in the Analysis of Electromigration and Stress Migration in Large Multisegment Interconnects

Nestor Evmorfopoulos¹, Mohammad Shohel², Olympia Axelou¹, Pavlos Stoikos¹, Vidya A. Chhabria², Sachin S. Sapatnekar²

¹Univ. of Thessaly, Volos, Greece ²Univ. of Minnesota, MN, USA

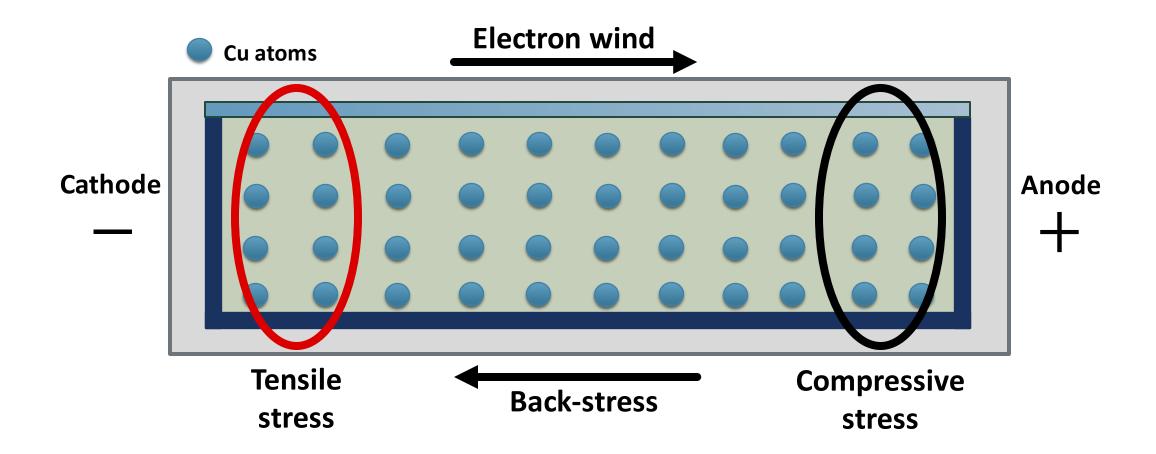




Outline

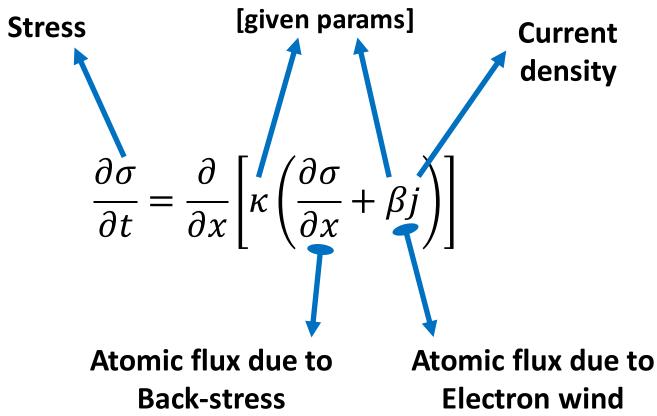
- Introduction
- Electromigration (EM) and Stress Migration Background
- EM/Stress Migration Analyses
- Multisegment Lines: Analytical Solution by Reflections
- Multisegment Lines: Semi-Analytical Solution
- Interconnect Trees: Semi-Analytical Solution
- Conclusion and Future Challenges

EM/Stress Migration Background



EM/Stress Migration Background

Physics-based modeling ∂ (Korhonen et al., JAP 1993) ∂



- Diffusion-type Partial Differential Equation
- Must hold in every segment of the interconnect

EM/Stress Migration Background

Boundary Conditions

Blocking terminal

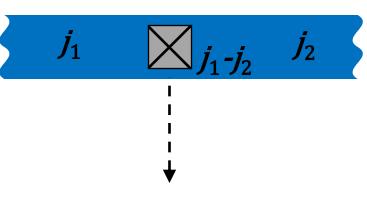


$$\frac{\partial \sigma}{\partial x} + \beta j = 0$$

Stress continuity

Conservation of atomic flux

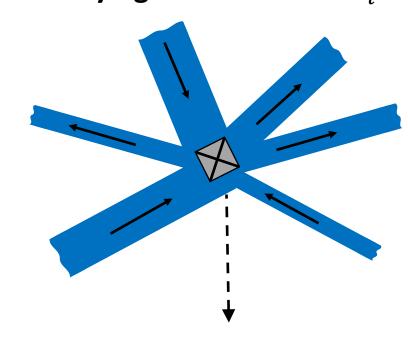
Intermediate point of multisegment line



$$\sigma_1 = \sigma_2$$

$$\frac{\partial \sigma_1}{\partial x} + \beta j_1 = \frac{\partial \sigma_2}{\partial x} + \beta j_2$$

Junction of N segments with varying cross-sections a_i



$$\sigma_1 = \cdots = \sigma_N$$

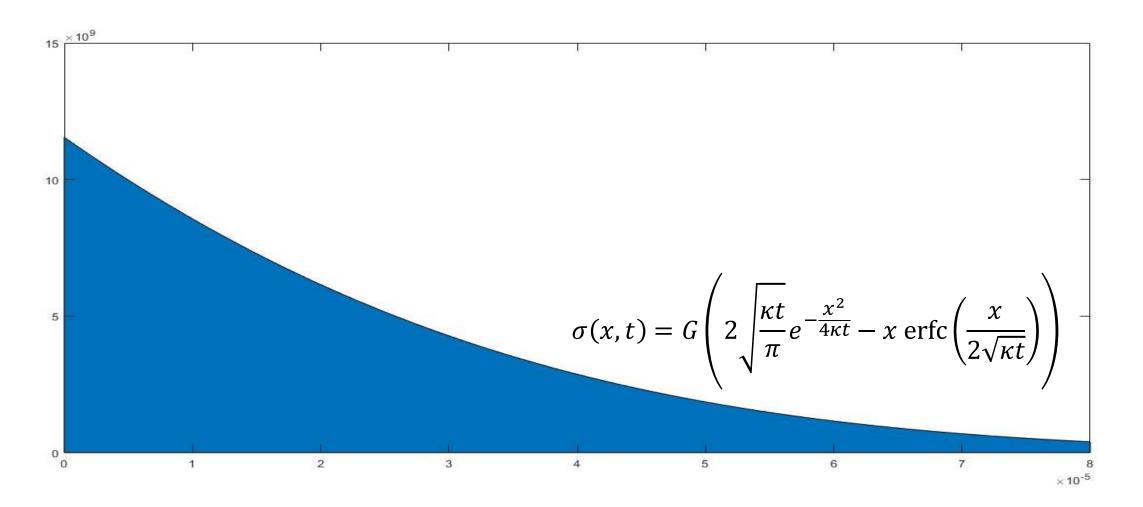
$$\frac{\partial \sigma_1}{\partial x} + \beta j_1 = \frac{\partial \sigma_2}{\partial x} + \beta j_2 \qquad \sum_{i=1}^{N_out} a_i \left(\frac{\partial \sigma_i}{\partial x} + \beta j_i \right) = \sum_{i=1}^{N_in} a_i \left(\frac{\partial \sigma_i}{\partial x} + \beta j_i \right)$$

EM/Stress Migration Analyses

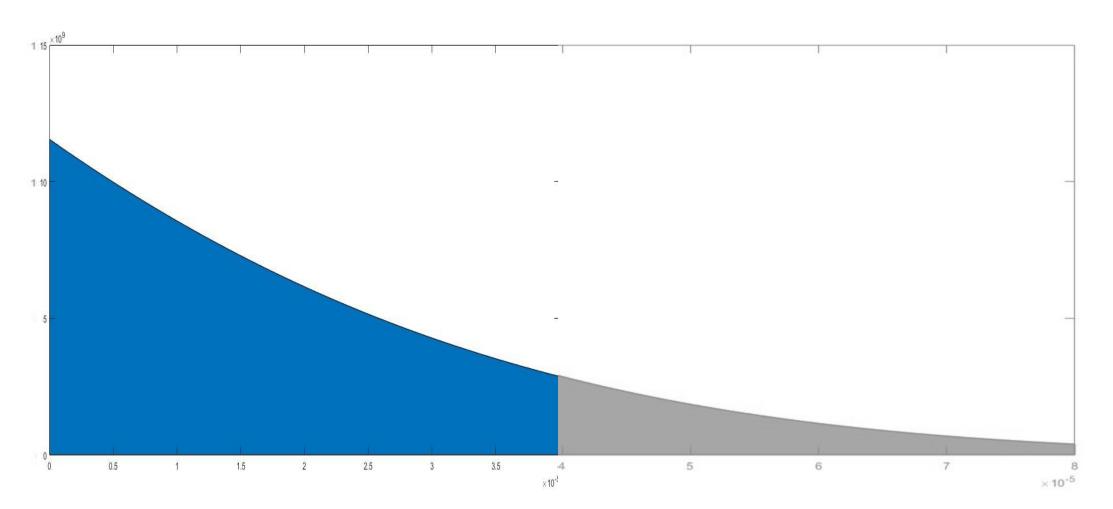
- If tensile stress exceeds critical value ⇒ void is nucleated (further electron wind leads to void growth, and eventual open circuit)
- Steady-state analysis
 - Solution for $t \to \infty$ (when transients have settled and driving forces reach equilibrium)
 - Can take very long time to reach (much longer than the expected chip lifetime)
 - Used to identify wires where critical stress is never attained (⇒ immortal wires)
 - Quite mature
- Transient analysis
 - Stress evolution over time
 - Identifies if potentially mortal wires from steady-state analysis are susceptible to EM
 (⇒ can attain critical stress) during chip lifetime



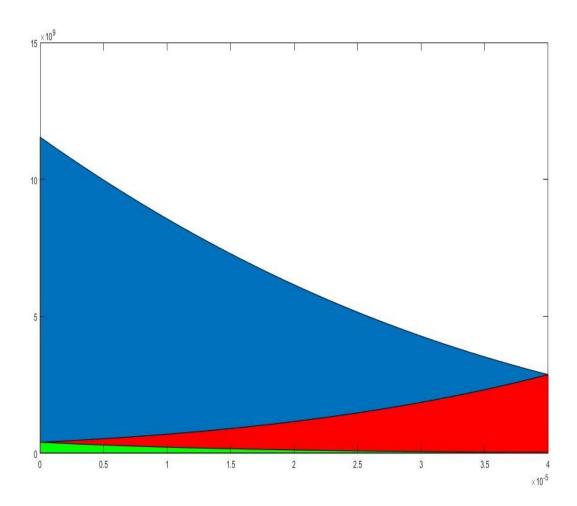
$$\frac{\partial \sigma}{\partial x} = -\beta j \equiv -G$$



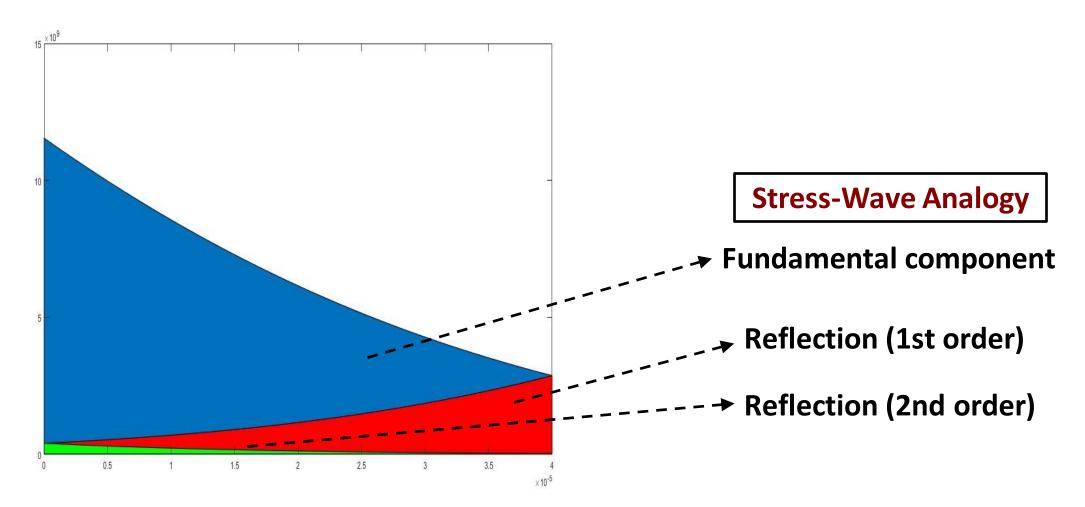




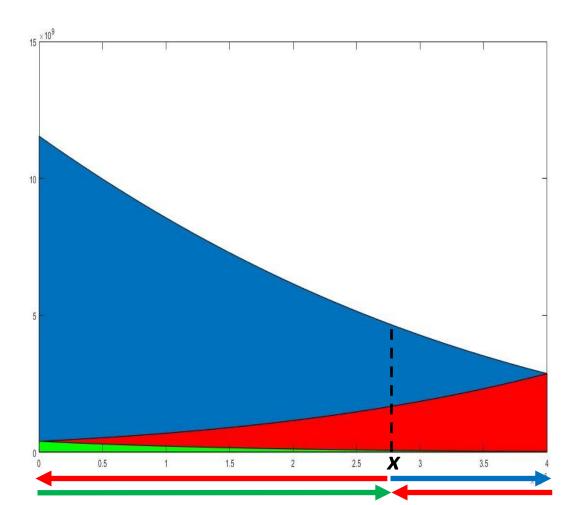




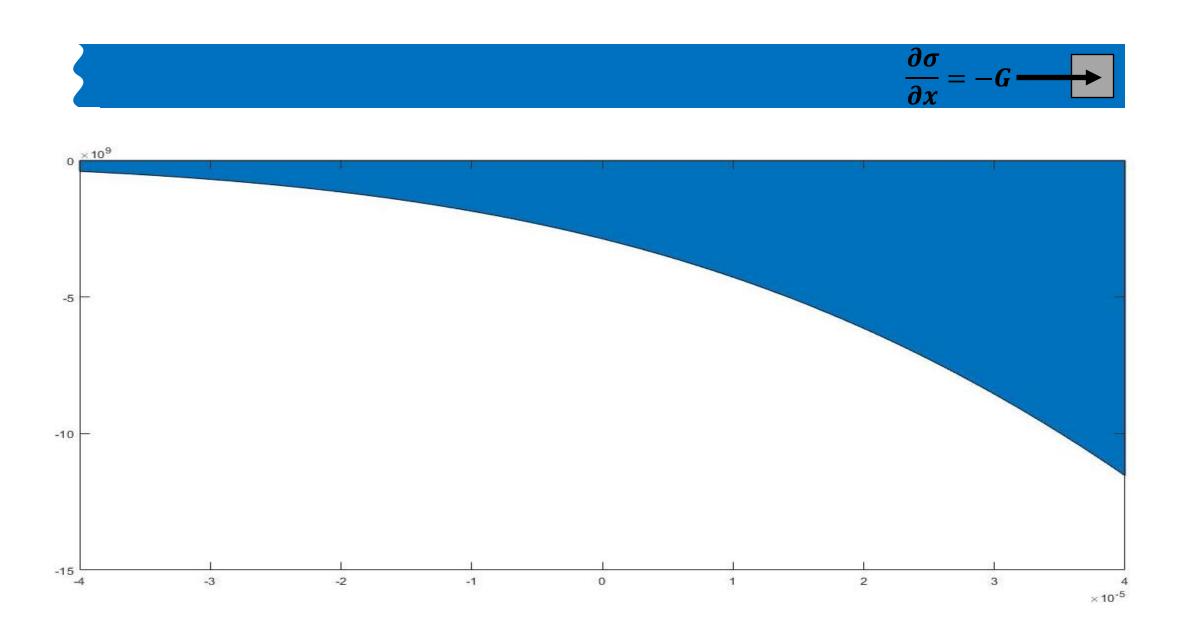


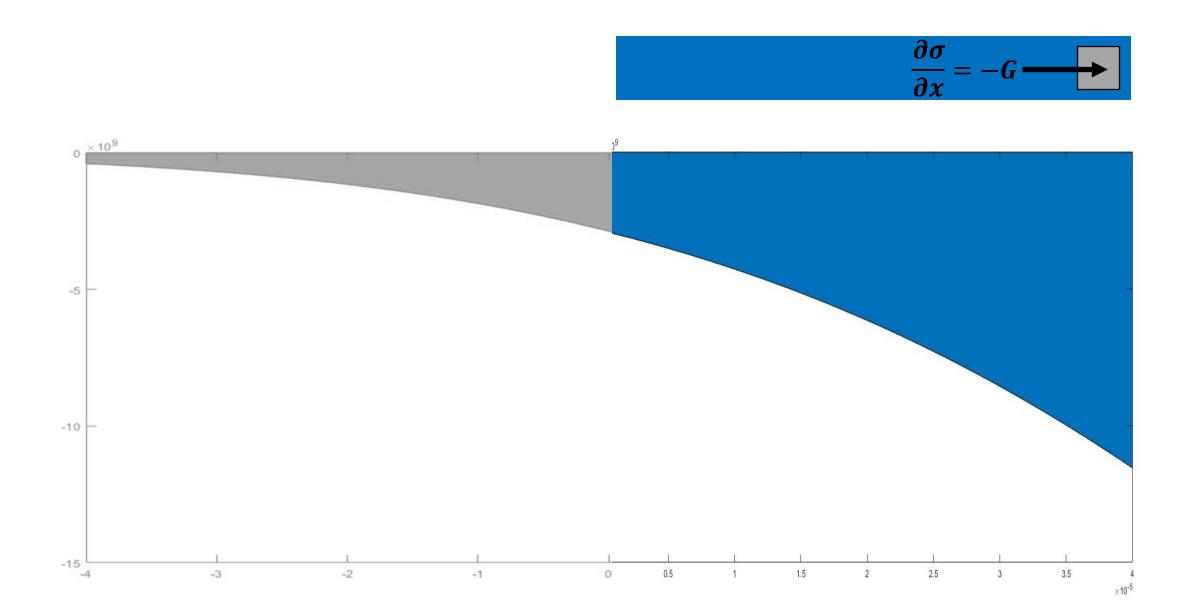




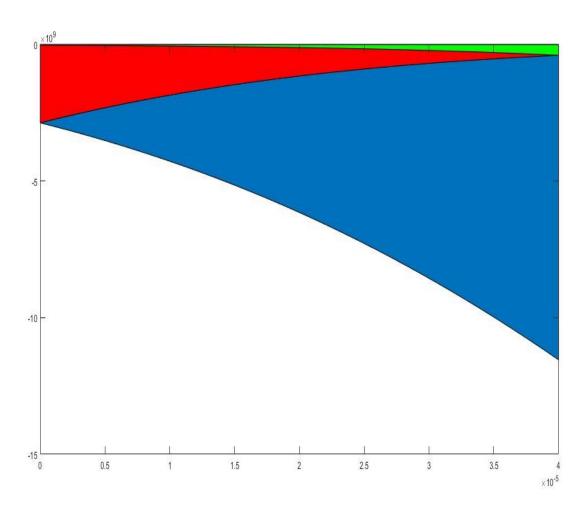


$$\frac{\partial \sigma}{\partial x} = -G \qquad \frac{\partial \sigma}{\partial x} = -G \longrightarrow$$

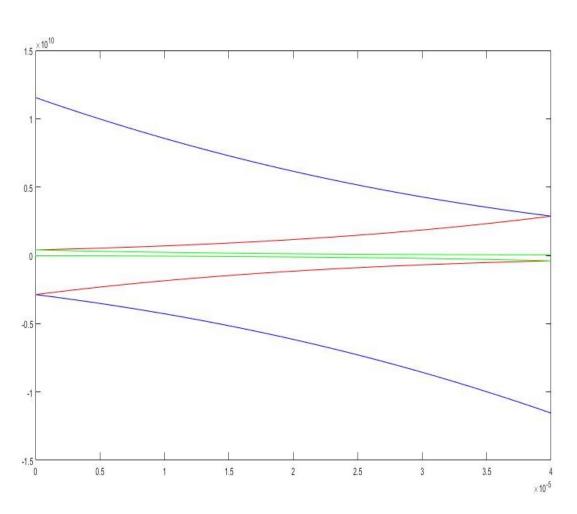




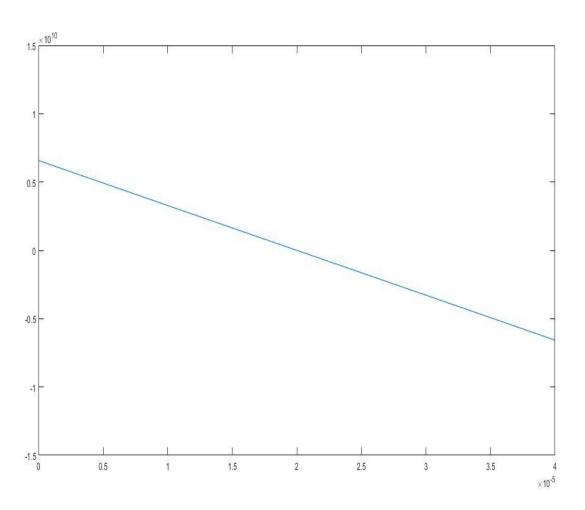




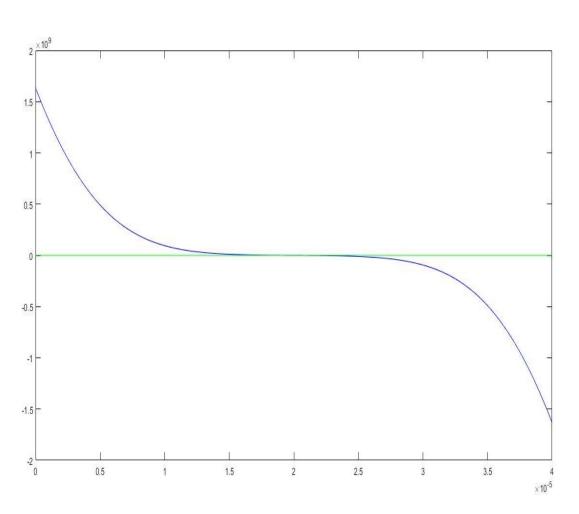




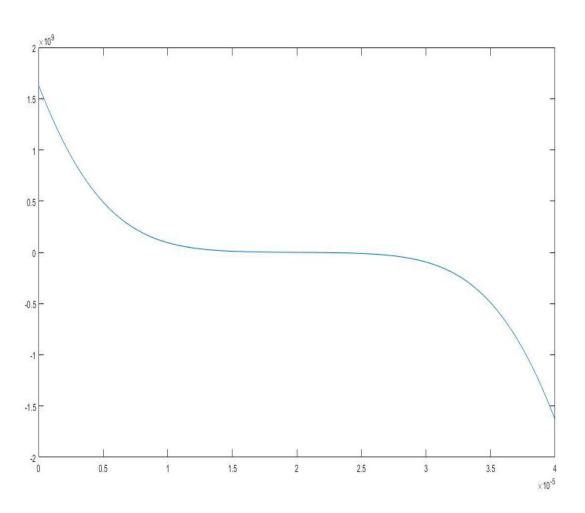


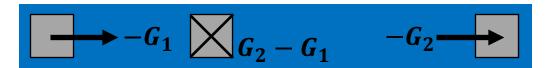


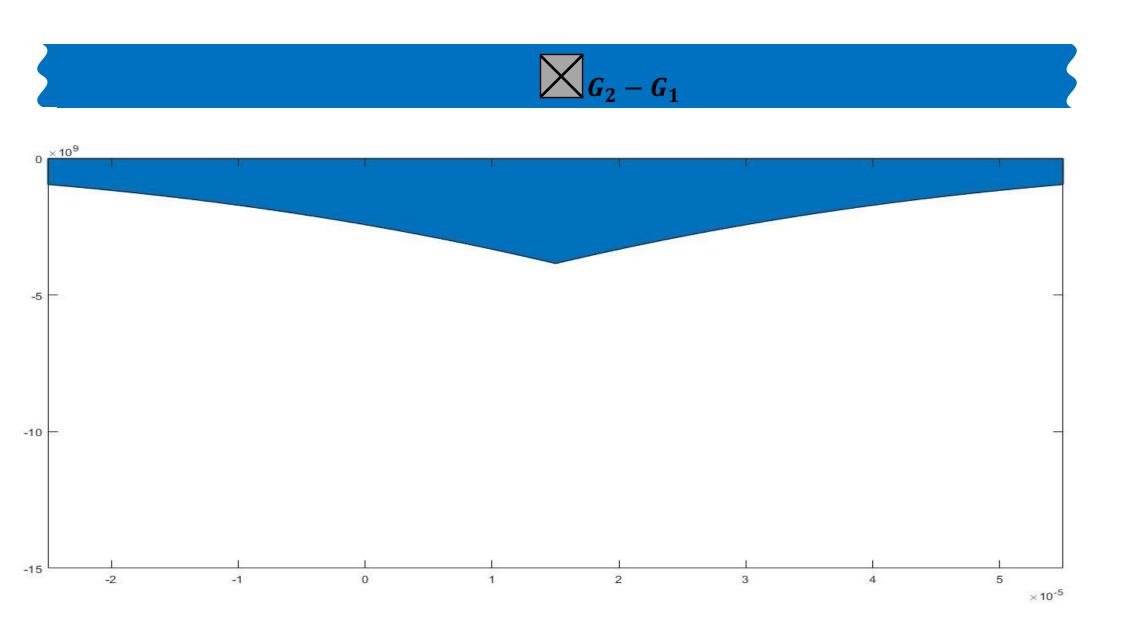


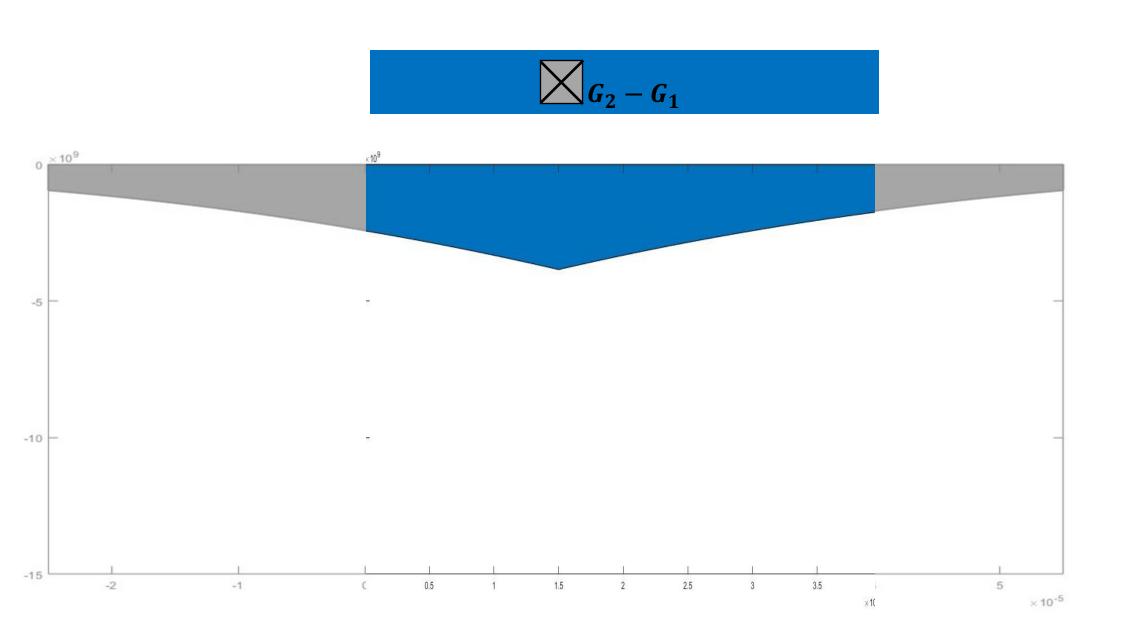


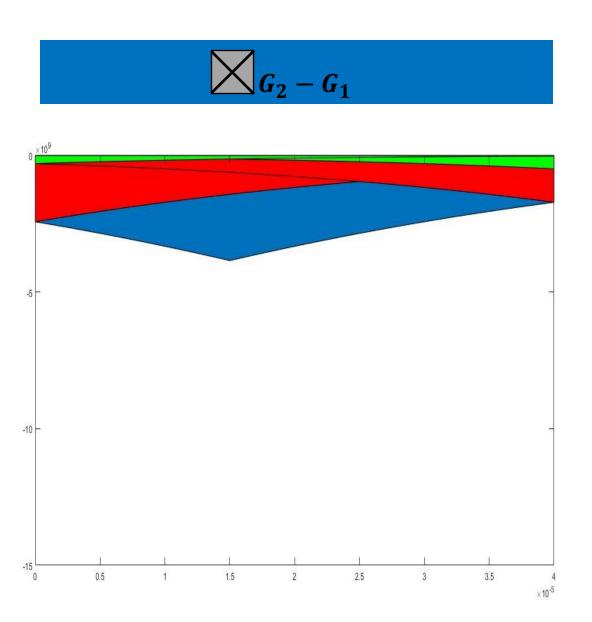


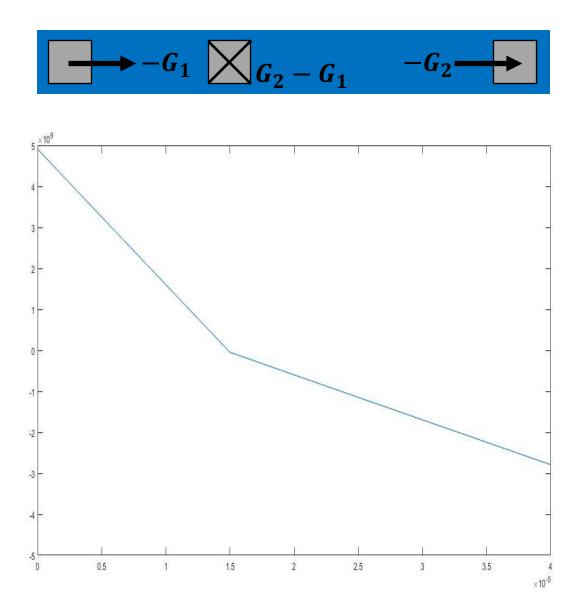


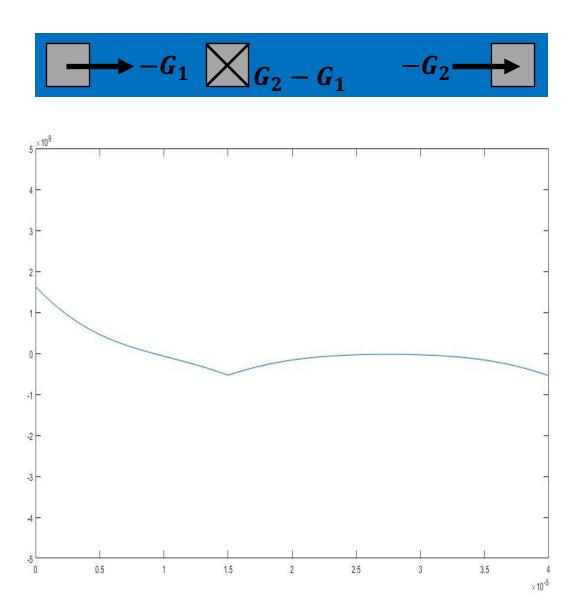






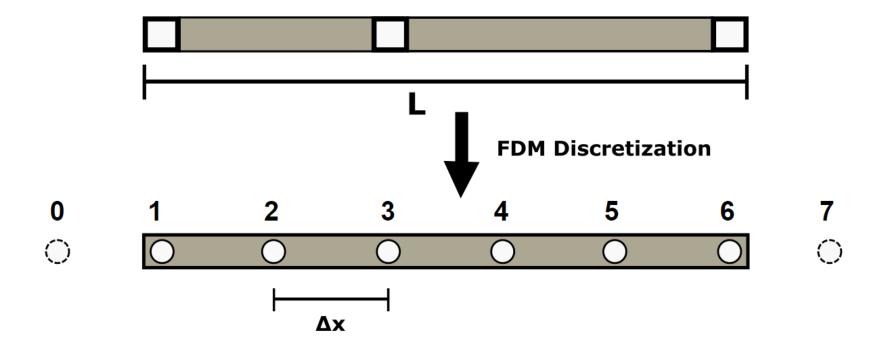


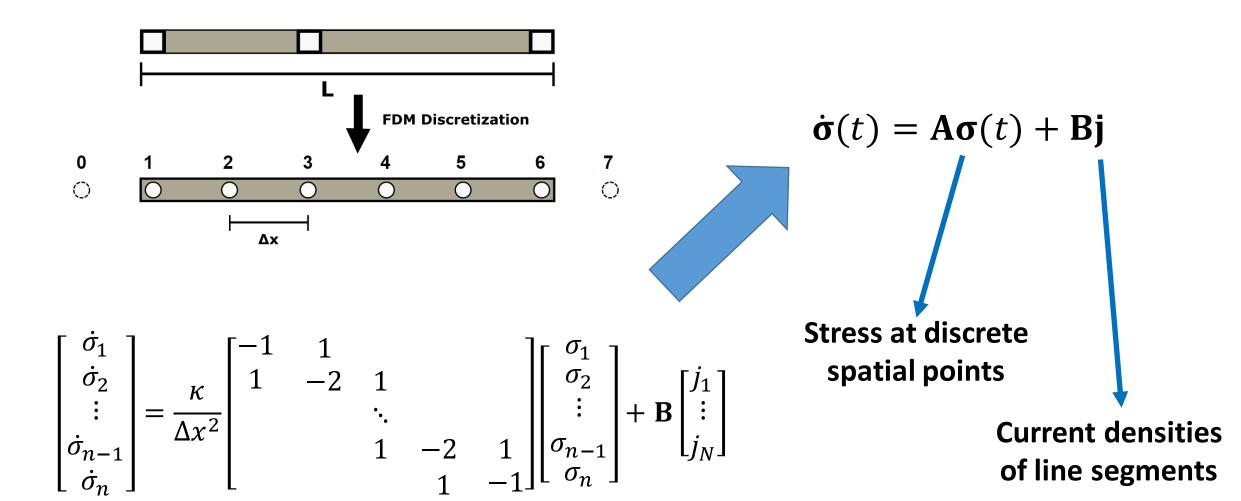


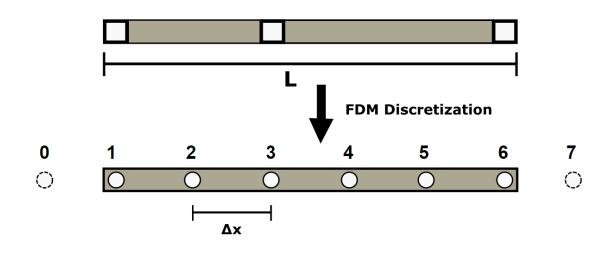


Multisegment line: solution by reflections

$$\begin{split} \sigma(x,t) &\approx G_1 \left[g\left(x,t \right) + g\left(2L_N - x,t \right) + g\left(2L_N + x,t \right) \right] \\ &- G_N \left[g\left(L_N - x,t \right) + g\left(L_N + x,t \right) + g\left(3L_N - x,t \right) \right] \\ &+ \sum_{i=1}^{N-1} \frac{G_{i+1} - G_i}{2} \left[g\left(|L_i - x|,t \right) + g\left(L_i + x,t \right) \right. \\ &+ g\left(L_i + 2L_N - x,t \right) + g\left(-L_i + 2L_N - x,t \right) \\ &+ g\left(-L_i + 2L_N + x,t \right) \right] \\ g(x,t) &= 2 \sqrt{\frac{\kappa t}{\pi}} e^{-\frac{x^2}{4\kappa t}} - x \operatorname{erfc}\left(\frac{x}{2\sqrt{\kappa t}} \right) \end{split}$$

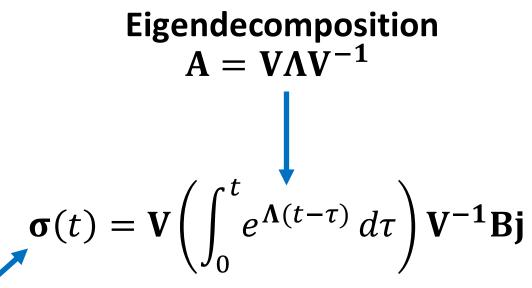






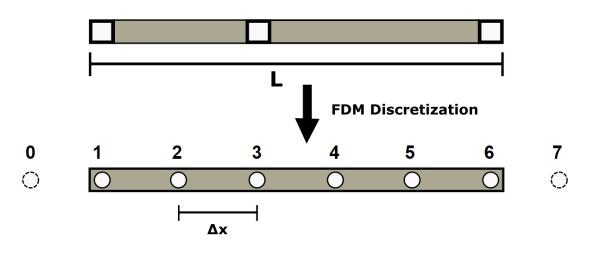
$$\dot{\sigma}(t) = \mathbf{A}\sigma(t) + \mathbf{B}\mathbf{j}$$

$$\sigma(t) = \int_0^t e^{\mathbf{A}(t-\tau)} \mathbf{B}\mathbf{j} d\tau$$



For each eigenvalue λ_i :

$$\int_0^t e^{\lambda_j(t-\tau)} d\tau = \begin{cases} \frac{e^{\lambda_j t} - 1}{\lambda_j}, & \lambda_j \neq 0 \\ t, & \lambda_j = 0 \end{cases}$$



$$\mathbf{A} = \frac{\kappa}{\Delta x^2} \begin{bmatrix} -1 & 1 & & & \\ 1 & -2 & 1 & & \\ & & \ddots & & \\ & & 1 & -2 & 1 \\ & & & 1 & -1 \end{bmatrix}$$

$$\lambda_j = \frac{\kappa}{\Delta x^2} \left(2 \cos \frac{(j-1)\pi}{n} - 2 \right), \quad j = 1, \dots, n$$

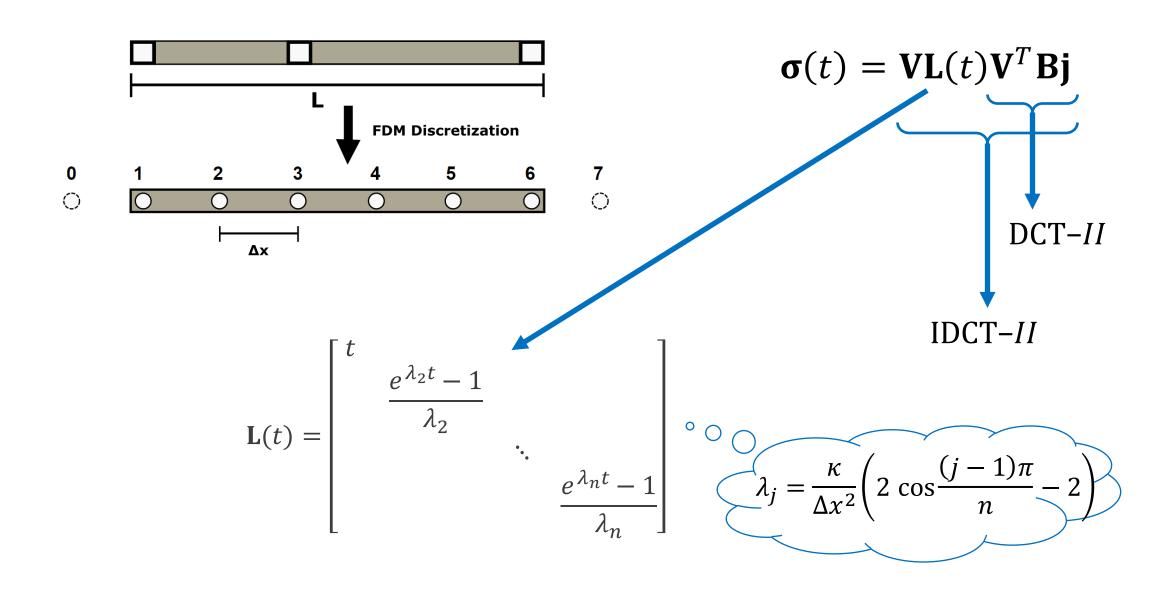
$$\mathbf{V}^{-1}\mathbf{r} \equiv \mathbf{V}^{T}\mathbf{r} \Leftrightarrow \mathrm{DCT}-II(\mathbf{r})$$

$$\mathbf{V}\mathbf{r} \Leftrightarrow \mathrm{IDCT}-II(\mathbf{r})$$

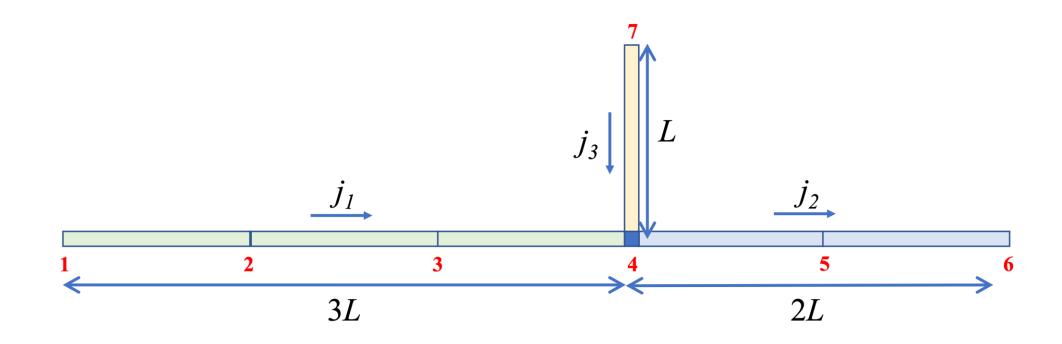
$$0(n\log n)$$

$$\mathbf{V} \mathbf{r} \Leftrightarrow \mathrm{IDCT}$$
- $II(\mathbf{r})$

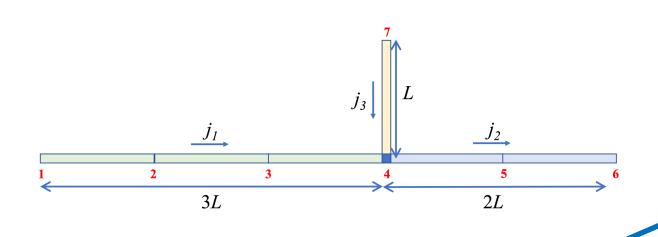




Interconnect tree: semi-analytical solution



Interconnect tree: semi-analytical solution

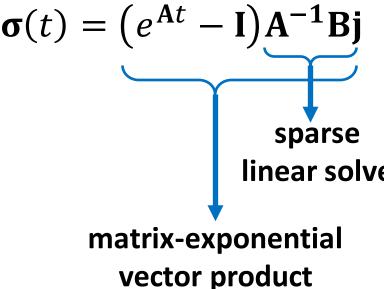


Conservation of atomic flux over the *entire* tree relates stress at discretized points

Solve for any σ_i and substitute

$$\dot{\sigma}(t) = A\sigma(t) + Bj$$

$$\sigma(t) = \int_0^t e^{A(t-\tau)} Bj d\tau$$



Conclusion and Future Challenges

Recent EM/Stress solutions for multisegment structures

- Reflections and stress-wave analogy for multisegment lines
 - → analytical calculation of stress via closed-form expression
- Semi-analytical solutions for multisegment lines and interconnect trees
 - → discretize only space, able to calculate stress at any future time directly Future challenges and perspectives
- Extend reflections framework and stress-wave analogy to interconnect trees
- Adapt analytical and semi-analytical solutions to growth phase
- Handling of time-varying (or frequency-specific) input current densities
- Design connections (lifetime-driven P&R, segment widths, P/G stripe spacing)
- Adoption of physics-based models and emerging solutions in industrial flows

Thank you!

Questions / Comments

nestevmo@uth.gr

